

EAST - [temp.wsp:1]

File View Edit Tools Window Help

☐ Drafts
☐ BRS:
☐ Pending
☒ Active
 L1: (1341) single adj2 poly
 L2: (44680) eeprom
 L3: (1256150) memory
 L4: (150) 1 adj5 (2 or 3)
 L5: (113484) erase or erasing or erased or erases
 L6: (45) 4 same 5
☐ Failed
 (0) eras3
☐ Saved
☐ Favorites
☐ Tagged (0)
☐ UDC
☐ Queue
☐ Trash

Search
 DBs: ☐ Plural
 Default operator: ☒ Highlight all hit terms initially
 4 same 5

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	F
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20020179965 A1	20021205	16	Non-volatile semiconductor memory d	257/316	257/E27.103	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020038882 A1	20020404	9	ELECTRICALLY ERASABLE, PROGRAMMABLE	257/314	257/316;	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020018364 A1	20020214	16	Non-volatile semiconductor memory d	365/185.02	257/E27.103	<input type="checkbox"/>
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020015327 A1	20020207	13	Low voltage flash EEPROM memory cel	365/185.03	257/E27.103	<input type="checkbox"/>
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6512700 B1	20030128	9	Non-volatile memory cell having cha	365/185.28	257/316;	<input type="checkbox"/>
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6512691 B2	20030128	15	Non-volatile memory embedded in a c	365/185.05	365/149;	<input type="checkbox"/>
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6501124 B2	20021231	13	Non-volatile semiconductor memory d	257/316	257/317;	<input type="checkbox"/>
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6450615 B1	20021001	10	Non-volatile memory cell operati	365/185.1	365/185.20	<input type="checkbox"/>